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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I ² C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	149
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 29x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5606bk0mlu6

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PA[15]	PCR[15]	AF0 AF1 AF2 AF3 —	GPIO[15] CS0_0 SCK_0 E0UC[1] WKUP[10] ⁴	SIUL DSPI_0 DSPI_0 eMIOS_0 WKUP	I/O I/O I/O I/O I	M	Tristate	27	40	48
Port B										
PB[0]	PCR[16]	AF0 AF1 AF2 AF3	GPIO[16] CAN0TX E0UC[30] LIN0TX	SIUL FlexCAN_0 eMIOS_0 LINFlex_0	I/O O I/O O	M	Tristate	23	31	39
PB[1]	PCR[17]	AF0 AF1 AF2 AF3 — — —	GPIO[17] — E0UC[31] — WKUP[4] ⁴ CAN0RX LIN0RX	SIUL — eMIOS_0 — WKUP FlexCAN_0 LINFlex_0	I/O — I/O — — — —	S	Tristate	24	32	40
PB[2]	PCR[18]	AF0 AF1 AF2 AF3	GPIO[18] LIN0TX SDA E0UC[30]	SIUL LINFlex_0 I ² C_0 eMIOS_0	I/O O I/O I/O	M	Tristate	100	144	176
PB[3]	PCR[19]	AF0 AF1 AF2 AF3 — —	GPIO[19] E0UC[31] SCL — WKUP[11] ⁴ LIN0RX	SIUL eMIOS_0 I ² C_0 — WKUP LINFlex_0	I/O I/O I/O — — —	S	Tristate	1	1	1
PB[4]	PCR[20]	AF0 AF1 AF2 AF3 — — —	— — — — ADC0_P[0] ADC1_P[0] GPIO[20]	— — — — ADC_0 ADC_1 SIUL	— — — — I — —	I	Tristate	50	72	88
PB[5]	PCR[21]	AF0 AF1 AF2 AF3 — — —	— — — — ADC0_P[1] ADC1_P[1] GPIO[21]	— — — — ADC_0 ADC_1 SIUL	— — — — I — —	I	Tristate	53	75	91

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number			
								100 LQFP	144 LQFP	176 LQFP	
PB[6]	PCR[22]	AF0 AF1 AF2 AF3 — — —	— — — — ADC0_P[2] ADC1_P[2] GPIO[22]	— — — — ADC_0 ADC_1 SIUL	— — — — — — —	I	Tristate	54	76	92	
PB[7]	PCR[23]	AF0 AF1 AF2 AF3 — — —	— — — — ADC0_P[3] ADC1_P[3] GPIO[23]	— — — — ADC_0 ADC_1 SIUL	— — — — — — —	I	Tristate	55	77	93	
PB[8]	PCR[24]	AF0 AF1 AF2 AF3 — — — —	GPIO[24] — — — OSC32K_XTAL ⁷ WKUP[25] ADC0_S[0] ADC1_S[4]	SIUL — — — OSC32K WKUP ADC_0 ADC_1	 — — — — — — 	I	—	39	53	61	
PB[9]	PCR[25]	AF0 AF1 AF2 AF3 — — — —	GPIO[25] — — — OSC32K_EXTAL ⁷ WKUP[26] ADC0_S[1] ADC1_S[5]	SIUL — — — OSC32K WKUP ADC_0 ADC_1	 — — — — — — 	I	—	38	52	60	
PB[10]	PCR[26]	AF0 AF1 AF2 AF3 — — —	GPIO[26] — — — WKUP[8] ⁴ ADC0_S[2] ADC1_S[6]	SIUL — — — WKUP ADC_0 ADC_1	 — — — — — — 	I/O	J	Tristate	40	54	62
PB[11]	PCR[27]	AF0 AF1 AF2 AF3 —	GPIO[27] E0UC[3] — CS0_0 ADC0_S[3]	SIUL eMIOS_0 — DSPI_0 ADC_0	 I/O — I/O 	I/O	J	Tristate	—	—	97
PB[12]	PCR[28]	AF0 AF1 AF2 AF3 —	GPIO[28] E0UC[4] — CS1_0 ADC0_X[0]	SIUL eMIOS_0 — DSPI_0 ADC_0	 I/O — O 	I/O	J	Tristate	61	83	101

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PD[13]	PCR[61]	AF0 AF1 AF2 AF3 —	GPIO[61] CS0_1 E0UC[25] — ADC0_S[5]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O I/O I/O — I	J	Tristate	62	84	102
PD[14]	PCR[62]	AF0 AF1 AF2 AF3 —	GPIO[62] CS1_1 E0UC[26] — ADC0_S[6]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O O I/O — I	J	Tristate	64	86	104
PD[15]	PCR[63]	AF0 AF1 AF2 AF3 —	GPIO[63] CS2_1 E0UC[27] — ADC0_S[7]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O O I/O — I	J	Tristate	66	88	106
Port E										
PE[0]	PCR[64]	AF0 AF1 AF2 AF3 — —	GPIO[64] E0UC[16] — — WKUP[6] ⁴ CAN5RX	SIUL eMIOS_0 — — WKUP FlexCAN_5	I/O I/O — — I I	S	Tristate	6	10	18
PE[1]	PCR[65]	AF0 AF1 AF2 AF3	GPIO[65] E0UC[17] CAN5TX —	SIUL eMIOS_0 FlexCAN_5 —	I/O I/O O —	M	Tristate	8	12	20
PE[2]	PCR[66]	AF0 AF1 AF2 AF3 — —	GPIO[66] E0UC[18] — — EIRQ[21] SIN_1	SIUL eMIOS_0 — — SIUL DSPI_1	I/O I/O — — I I	M	Tristate	89	128	156
PE[3]	PCR[67]	AF0 AF1 AF2 AF3 —	GPIO[67] E0UC[19] SOUT_1 —	SIUL eMIOS_0 DSPI_1 —	I/O I/O O —	M	Tristate	90	129	157
PE[4]	PCR[68]	AF0 AF1 AF2 AF3 —	GPIO[68] E0UC[20] SCK_1 — EIRQ[9]	SIUL eMIOS_0 DSPI_1 — SIUL	I/O I/O I/O — I	M	Tristate	93	132	160
PE[5]	PCR[69]	AF0 AF1 AF2 AF3	GPIO[69] E0UC[21] CS0_1 MA[2]	SIUL eMIOS_0 DSPI_1 ADC_0	I/O I/O I/O O	M	Tristate	94	133	161

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PE[6]	PCR[70]	AF0 AF1 AF2 AF3 —	GPIO[70] E0UC[22] CS3_0 MA[1] EIRQ[22]	SIUL eMIOS_0 DSPI_0 ADC_0 SIUL	I/O I/O O O I	M	Tristate	95	139	167
PE[7]	PCR[71]	AF0 AF1 AF2 AF3 —	GPIO[71] E0UC[23] CS2_0 MA[0] EIRQ[23]	SIUL eMIOS_0 DSPI_0 ADC_0 SIUL	I/O I/O O O I	M	Tristate	96	140	168
PE[8]	PCR[72]	AF0 AF1 AF2 AF3	GPIO[72] CAN2TX E0UC[22] CAN3TX	SIUL FlexCAN_2 eMIOS_0 FlexCAN_3	I/O O I/O O	M	Tristate	9	13	21
PE[9]	PCR[73]	AF0 AF1 AF2 AF3 — — —	GPIO[73] — E0UC[23] — WKUP[7] ⁴ CAN2RX CAN3RX	SIUL — eMIOS_0 — WKUP FlexCAN_2 FlexCAN_3	I/O — I/O — I — I	S	Tristate	10	14	22
PE[10]	PCR[74]	AF0 AF1 AF2 AF3 —	GPIO[74] LIN3TX CS3_1 E1UC[30] EIRQ[10]	SIUL LINFLEX_3 DSPI_1 eMIOS_1 SIUL	I/O O O I/O I	S	Tristate	11	15	23
PE[11]	PCR[75]	AF0 AF1 AF2 AF3 — —	GPIO[75] E0UC[24] CS4_1 — LIN3RX WKUP[14] ⁴	SIUL eMIOS_0 DSPI_1 — LINFLEX_3 WKUP	I/O I/O O — I I	S	Tristate	13	17	25
PE[12]	PCR[76]	AF0 AF1 AF2 AF3 — — —	GPIO[76] — E1UC[19] ¹⁰ — EIRQ[11] SIN_2 ADC1_S[7]	SIUL — eMIOS_1 — SIUL DSPI_2 ADC_1	I/O — I/O — I — I	J	Tristate	76	109	133
PE[13]	PCR[77]	AF0 AF1 AF2 AF3	GPIO[77] SOUT_2 E1UC[20] —	SIUL DSPI_2 eMIOS_1 —	I/O O I/O —	S	Tristate	—	103	127

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function ¹	Function	Peripheral	I/O direction	Pad type ²	RESET config. ³	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PG[7]	PCR[103]	AF0 AF1 AF2 AF3 — —	GPIO[103] E1UC[16] E1UC[30] — WKUP[20] ⁴ LIN6RX	SIUL eMIOS_1 eMIOS_1 — WKUP LINFlex_6	I/O I/O I/O — I I	S	Tristate	—	29	37
PG[8]	PCR[104]	AF0 AF1 AF2 AF3 —	GPIO[104] E1UC[17] LIN7TX CS0_2 EIRQ[15]	SIUL eMIOS_1 LINFlex_7 DSPI_2 SIUL	I/O I/O O I/O I	S	Tristate	—	26	34
PG[9]	PCR[105]	AF0 AF1 AF2 AF3 — —	GPIO[105] E1UC[18] — SCK_2 WKUP[21] ⁴ LIN7RX	SIUL eMIOS_1 — DSPI_2 WKUP LINFlex_7	I/O I/O — I/O I I	S	Tristate	—	25	33
PG[10]	PCR[106]	AF0 AF1 AF2 AF3 —	GPIO[106] E0UC[24] E1UC[31] — SIN_4	SIUL eMIOS_0 eMIOS_1 — DSPI_4	I/O I/O I/O — I	S	Tristate	—	114	138
PG[11]	PCR[107]	AF0 AF1 AF2 AF3	GPIO[107] E0UC[25] CS0_4 —	SIUL eMIOS_0 DSPI_4 —	I/O I/O O —	M	Tristate	—	115	139
PG[12]	PCR[108]	AF0 AF1 AF2 AF3	GPIO[108] E0UC[26] SOUT_4 —	SIUL eMIOS_0 DSPI_4 —	I/O I/O O —	M	Tristate	—	92	116
PG[13]	PCR[109]	AF0 AF1 AF2 AF3	GPIO[109] E0UC[27] SCK_4 —	SIUL eMIOS_0 DSPI_4 —	I/O I/O I/O —	M	Tristate	—	91	115
PG[14]	PCR[110]	AF0 AF1 AF2 AF3	GPIO[110] E1UC[0] — —	SIUL eMIOS_1 — —	I/O I/O — —	S	Tristate	—	110	134
PG[15]	PCR[111]	AF0 AF1 AF2 AF3 —	GPIO[111] E1UC[1] — — —	SIUL eMIOS_1 — — —	I/O I/O — — —	M	Tristate	—	111	135
Port H										

K is a constant for the particular part, which may be determined from [Equation 3](#) by measuring P_D (at equilibrium) for a known T_A . Using this value of K , the values of P_D and T_J may be obtained by solving equations [1](#) and [2](#) iteratively for any value of T_A .

3.6 I/O pad electrical characteristics

3.6.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads — are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads — provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads — provide maximum speed. These are used for improved debugging capability.
- Input only pads — are associated with ADC channels and 32 kHz low power external crystal oscillator providing low input leakage.

Medium and Fast pads can use slow configuration to reduce electromagnetic emission, at the cost of reducing AC performance.

3.6.2 I/O input DC characteristics

[Table 12](#) provides input DC electrical characteristics as described in [Figure 5](#).

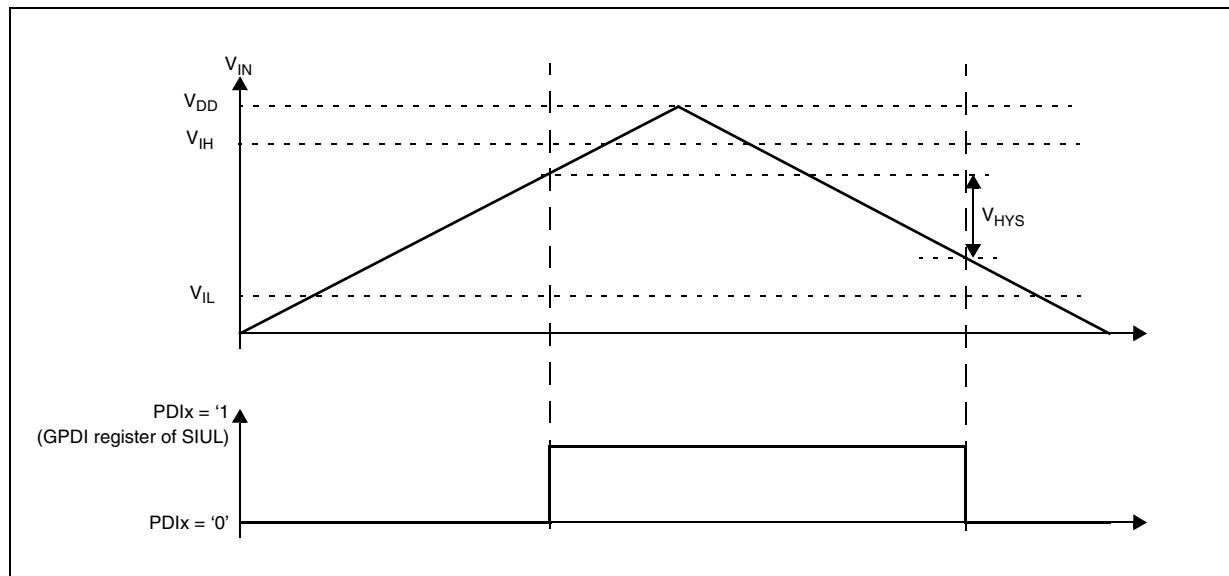


Figure 5. I/O input DC electrical characteristics definition

Table 12. I/O input DC electrical characteristics

Symbol	C	Parameter	Conditions ¹	Value			Unit	
				Min	Typ	Max		
V_{IH}	SR	P	Input high level CMOS (Schmitt Trigger)	—	$0.65V_{DD}$	—	$V_{DD} + 0.4$	
V_{IL}	SR	P	Input low level CMOS (Schmitt Trigger)	—	-0.4	—	$0.35V_{DD}$	
V_{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	—	$0.1V_{DD}$	—	—	
I_{LKG}	CC	P	Digital input leakage	No injection on adjacent pin	$T_A = -40\text{ }^{\circ}\text{C}$	—	2	nA
					$T_A = 25\text{ }^{\circ}\text{C}$	—	2	
					$T_A = 85\text{ }^{\circ}\text{C}$	—	5	
					$T_A = 105\text{ }^{\circ}\text{C}$	—	12	
					$T_A = 125\text{ }^{\circ}\text{C}$	—	70	
W_{FI}^2	SR	P	Wakeup input filtered pulse	—	—	—	40	ns
W_{NFI}^2	SR	P	Wakeup input not filtered pulse	—	1000	—	—	ns

¹ $V_{DD} = 3.3\text{ V} \pm 10\% / 5.0\text{ V} \pm 10\%$, $T_A = -40$ to $125\text{ }^{\circ}\text{C}$, unless otherwise specified

² In the range from 40 to 1000 ns, pulses can be filtered or not filtered, according to operating temperature and voltage.

3.6.3 I/O output DC characteristics

The following tables provide DC characteristics for bidirectional pads:

- Table 13 provides weak pull figures. Both pull-up and pull-down resistances are supported.
- Table 14 provides output driver characteristics for I/O pads when in SLOW configuration.
- Table 15 provides output driver characteristics for I/O pads when in MEDIUM configuration.
- Table 16 provides output driver characteristics for I/O pads when in FAST configuration.

Table 13. I/O pull-up/pull-down DC electrical characteristics

Symbol	C	Parameter	Conditions ¹	Value			Unit	
				Min	Typ	Max		
$ I_{WPUI} $	CC	P	Weak pull-up current absolute value	$V_{IN} = V_{IL}$, $V_{DD} = 5.0\text{ V} \pm 10\%$	PAD3V5V = 0	10	—	μA
					PAD3V5V = 1 ²	10	—	
				$V_{IN} = V_{IL}$, $V_{DD} = 3.3\text{ V} \pm 10\%$	PAD3V5V = 1	10	—	
$ I_{WPD} $	CC	P	Weak pull-down current absolute value	$V_{IN} = V_{IH}$, $V_{DD} = 5.0\text{ V} \pm 10\%$	PAD3V5V = 0	10	—	μA
					PAD3V5V = 1	10	—	
					PAD3V5V = 1	10	—	

¹ $V_{DD} = 3.3\text{ V} \pm 10\% / 5.0\text{ V} \pm 10\%$, $T_A = -40$ to $125\text{ }^{\circ}\text{C}$, unless otherwise specified.

² The configuration PAD3V5 = 1 when $V_{DD} = 5\text{ V}$ is only a transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

Table 19. I/O consumption (continued)

Symbol	C	Parameter	Conditions ¹			Value			Unit		
			Min	Typ	Max						
I_{RMSFST}	CC	D	Root medium square I/O current for FAST configuration	$C_L = 25 \text{ pF}, 40 \text{ MHz}$	$V_{DD} = 5.0 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 0$	—	—	22	mA		
				$C_L = 25 \text{ pF}, 64 \text{ MHz}$		—	—	33			
				$C_L = 100 \text{ pF}, 40 \text{ MHz}$		—	—	56			
				$C_L = 25 \text{ pF}, 40 \text{ MHz}$	$V_{DD} = 3.3 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 1$	—	—	14			
				$C_L = 25 \text{ pF}, 64 \text{ MHz}$		—	—	20			
				$C_L = 100 \text{ pF}, 40 \text{ MHz}$		—	—	35			
I_{AVGSEG}	SR	D	Sum of all the static I/O current within a supply segment	$V_{DD} = 5.0 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 0$			—	—	70	mA	
				$V_{DD} = 3.3 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 1$			—	—	65		

¹ $V_{DD} = 3.3 \text{ V} \pm 10\% / 5.0 \text{ V} \pm 10\%$, $T_A = -40$ to 125°C , unless otherwise specified

² Stated maximum values represent peak consumption that lasts only a few ns during I/O transition.

Table 20 provides the weight of concurrent switching I/Os.

In order to ensure device functionality, the sum of the weight of concurrent switching I/Os on a single segment should remain below the 100%.

Table 20. I/O weight¹

Supply segment			Pad	176 LQFP				144/100 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
				SRC ² = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
6	4	4	PB[3]	5%	—	6%	—	13%	—	15%	—
				4%	—	5%	—	13%	—	15%	—
				4%	—	4%	—	13%	—	15%	—
				3%	4%	4%	4%	12%	18%	15%	16%
	—	—	PJ[4]	3%	4%	3%	3%	—	—	—	—

Table 20. I/O weight¹ (continued)

Supply segment			Pad	176 LQFP				144/100 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
				SRC ² = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
176 LQFP	144 LQFP	100 LQFP									
2	1	—	PG[9]	9%	—	10%	—	9%	—	10%	—
		—	PG[8]	9%	—	11%	—	9%	—	11%	—
		1	PC[11]	9%	—	11%	—	9%	—	11%	—
			PC[10]	9%	13%	11%	12%	9%	13%	11%	12%
		—	PG[7]	9%	—	11%	—	9%	—	11%	—
		—	PG[6]	10%	14%	11%	12%	10%	14%	11%	12%
		1	PB[0]	10%	14%	12%	12%	10%	14%	12%	12%
			PB[1]	10%	—	12%	—	10%	—	12%	—
		—	PF[9]	10%	—	12%	—	10%	—	12%	—
		—	PF[8]	10%	14%	12%	13%	10%	14%	12%	13%
		—	PF[12]	10%	15%	12%	13%	10%	15%	12%	13%
		1	PC[6]	10%	—	12%	—	10%	—	12%	—
			PC[7]	10%	—	12%	—	10%	—	12%	—
		—	PF[10]	10%	14%	11%	12%	10%	14%	11%	12%
		—	PF[11]	9%	—	11%	—	9%	—	11%	—
		1	PA[15]	8%	12%	10%	10%	8%	12%	10%	10%
		—	PF[13]	8%	—	10%	—	8%	—	10%	—
		1	PA[14]	8%	11%	9%	10%	8%	11%	9%	10%
			PA[4]	7%	—	9%	—	7%	—	9%	—
			PA[13]	7%	10%	8%	9%	7%	10%	8%	9%
			PA[12]	7%	—	8%	—	7%	—	8%	—

3.8 Power management electrical characteristics

3.8.1 Voltage regulator electrical characteristics

The device implements an internal voltage regulator to generate the low voltage core supply V_{DD_LV} from the high voltage ballast supply V_{DD_BV} . The regulator itself is supplied by the common I/O supply V_{DD} . The following supplies are involved:

- HV: High voltage external power supply for voltage regulator module. This must be provided externally through V_{DD} power pin.
- BV: High voltage external power supply for internal ballast module. This must be provided externally through V_{DD_BV} power pin. Voltage values should be aligned with V_{DD} .
- LV: Low voltage internal power supply for core, FMPLL and Flash digital logic. This is generated by the internal voltage regulator but provided outside to connect stability capacitor. It is further split into four main domains to ensure noise isolation between critical LV modules within the device:
 - LV_COR: Low voltage supply for the core. It is also used to provide supply for FMPLL through double bonding.
 - LV_CFLA: Low voltage supply for code Flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
 - LV_DFLA: Low voltage supply for data Flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
 - LV_PLL: Low voltage supply for FMPLL. It is shorted to LV_COR through double bonding.

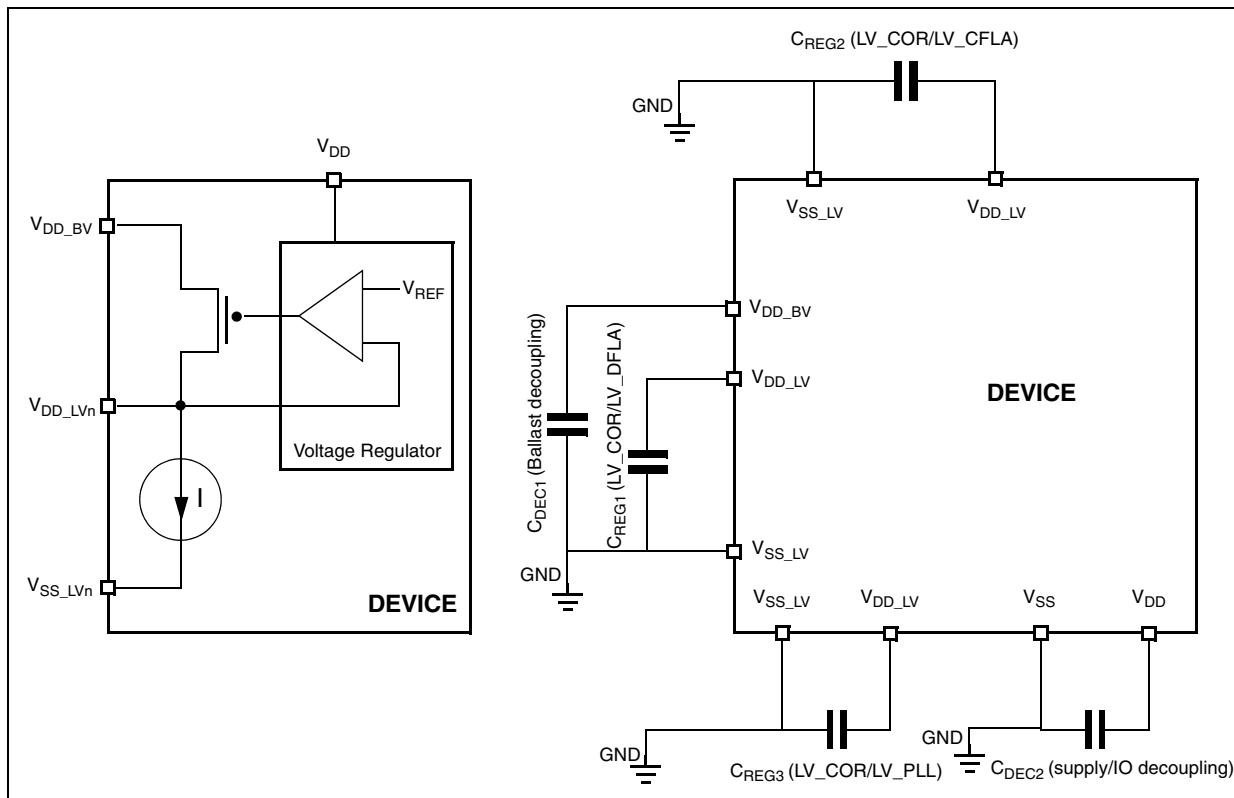


Figure 8. Voltage regulator capacitance connection

The internal voltage regulator requires external capacitance (C_{REGn}) to be connected to the device in order to provide a stable low voltage digital supply to the device. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the board to less than 5 nH.

3.9 Power consumption in different application modes

Table 24 provides DC electrical characteristics for significant application modes. These values are indicative values; actual consumption depends on the application.

Table 24. Electrical characteristics in different application modes¹

Symbol	C	Parameter	Conditions ²	Value			Unit		
				Min	Typ	Max			
I _{DDMAX} ³	CC	C	RUN mode maximum average current	—	81	130 ⁴	mA		
I _{DDRUN} ⁵	CC	T	RUN mode typical average current ⁶	f _{CPU} = 8 MHz	—	12	—		
		T		f _{CPU} = 16 MHz	—	27	—		
		C		f _{CPU} = 32 MHz	—	40	—		
		P		f _{CPU} = 48 MHz	—	54	95		
		P		f _{CPU} = 64 MHz	—	67	120		
I _{DDHALT}	CC	C	HALT mode current ⁷	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	10	15	mA
		P			T _A = 125 °C	—	15	28	
I _{DDSTOP}	CC	P	STOP mode current ⁸	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	130	500	μA
		D			T _A = 55 °C	—	180	—	
		D			T _A = 85 °C	—	1	5	
		D			T _A = 105 °C	—	3	9	
		P			T _A = 125 °C	—	5	14	
I _{DDSTDBY2}	CC	P	STANDBY2 mode current ⁹	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	17	80	μA
		C			T _A = 55 °C	—	30	—	
		C			T _A = 85 °C	—	110	—	
		C			T _A = 105 °C	—	280	950	
		C			T _A = 125 °C	—	460	1700	
I _{DDSTDBY1}	CC	C	STANDBY1 mode current ¹⁰	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	12	50	μA
		C			T _A = 55 °C	—	24	—	
		C			T _A = 85 °C	—	48	—	
		C			T _A = 105 °C	—	150	500	
		C			T _A = 125 °C	—	260	—	

¹ Except for I_{DDMAX}, all consumptions in this table apply to V_{DD_BV} only and do not include V_{DD_HV}.

² V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

³ Running consumption is given on voltage regulator supply (V_{DDREG}). I_{DDMAX} is composed of three components: I_{DDMAX} = I_{DD(VDD_BV)} + I_{DD(VDD_HV)} + I_{DD(VDD_HV_ADC)}. It does not include a fourth component linked to I/Os toggling which is **highly** dependent on the application. The given value is thought to be a **worst case value** (64 MHz at 125 °C) with all peripherals running, and code fetched from code flash while modify operation on-going on data flash. Note that this value can be significantly reduced by the application: switch off unused peripherals (default), reduce peripheral frequency through internal prescaler, fetch from RAM most used functions, use low power mode when possible.

Table 31. ESD absolute maximum ratings^{1,2}

Symbol	Ratings	Conditions	Class	Max value³	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	$T_A = 25^\circ\text{C}$ conforming to AEC-Q100-002	H1C	2000	V
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)	$T_A = 25^\circ\text{C}$ conforming to AEC-Q100-003	M2	200	
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charged Device Model)	$T_A = 25^\circ\text{C}$ conforming to AEC-Q100-011	C3A	500 750 (corners)	

¹ All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.

² A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

³ Data based on characterization results, not tested in production

3.11.3.2 Static latch-up (LU)

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with the EIA/JESD 78 IC latch-up standard.

Table 32. Latch-up results

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = 125^\circ\text{C}$ conforming to JESD 78	II level A

3.12 Fast external crystal oscillator (4 to 16 MHz) electrical characteristics

The device provides an oscillator/resonator driver. [Figure 12](#) describes a simple model of the internal oscillator driver and provides an example of a connection for an oscillator or a resonator.

[Table 33](#) provides the parameter description of 4 MHz to 16 MHz crystals used for the design simulations.

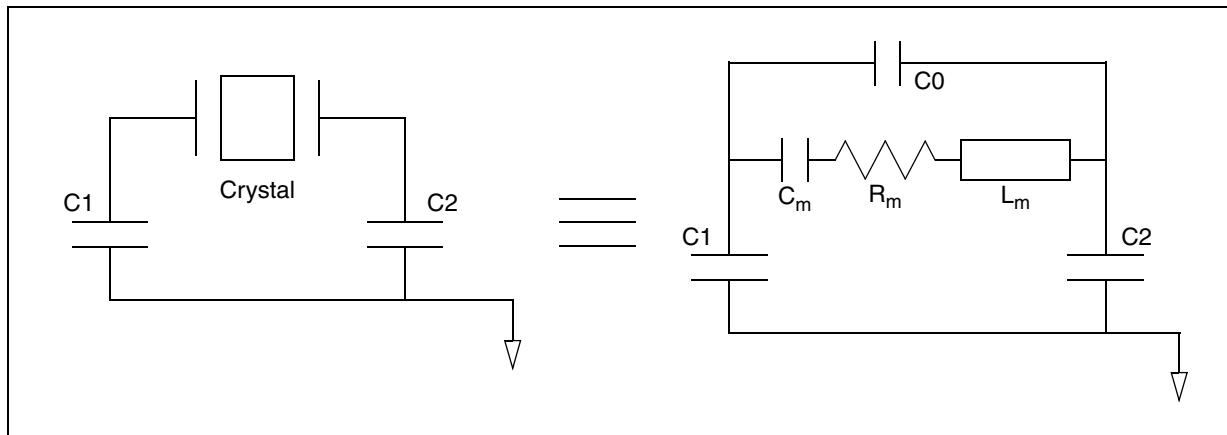


Figure 15. Equivalent circuit of a quartz crystal

Table 35. Crystal motional characteristics¹

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
L _m	Motional inductance	—	—	11.796	—	KH
C _m	Motional capacitance	—	—	2	—	fF
C1/C2	Load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground ²	—	18	—	28	pF
R _m ³	Motional resistance	AC coupled at C0 = 2.85 pF ⁴	—	—	65	kΩ
		AC coupled at C0 = 4.9 pF ⁴	—	—	50	
		AC coupled at C0 = 7.0 pF ⁴	—	—	35	
		AC coupled at C0 = 9.0 pF ⁴	—	—	30	

¹ The crystal used is Epson Toyocom MC306.

² This is the recommended range of load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground. It includes all the parasitics due to board traces, crystal and package.

³ Maximum ESR (R_m) of the crystal is 50 kΩ

⁴ C0 Includes a parasitic capacitance of 2.0 pF between OSC32K_XTAL and OSC32K_EXTAL pins.

3.17 ADC electrical characteristics

3.17.1 Introduction

The device provides two Successive Approximation Register (SAR) analog-to-digital converters (10-bit and 12-bit).

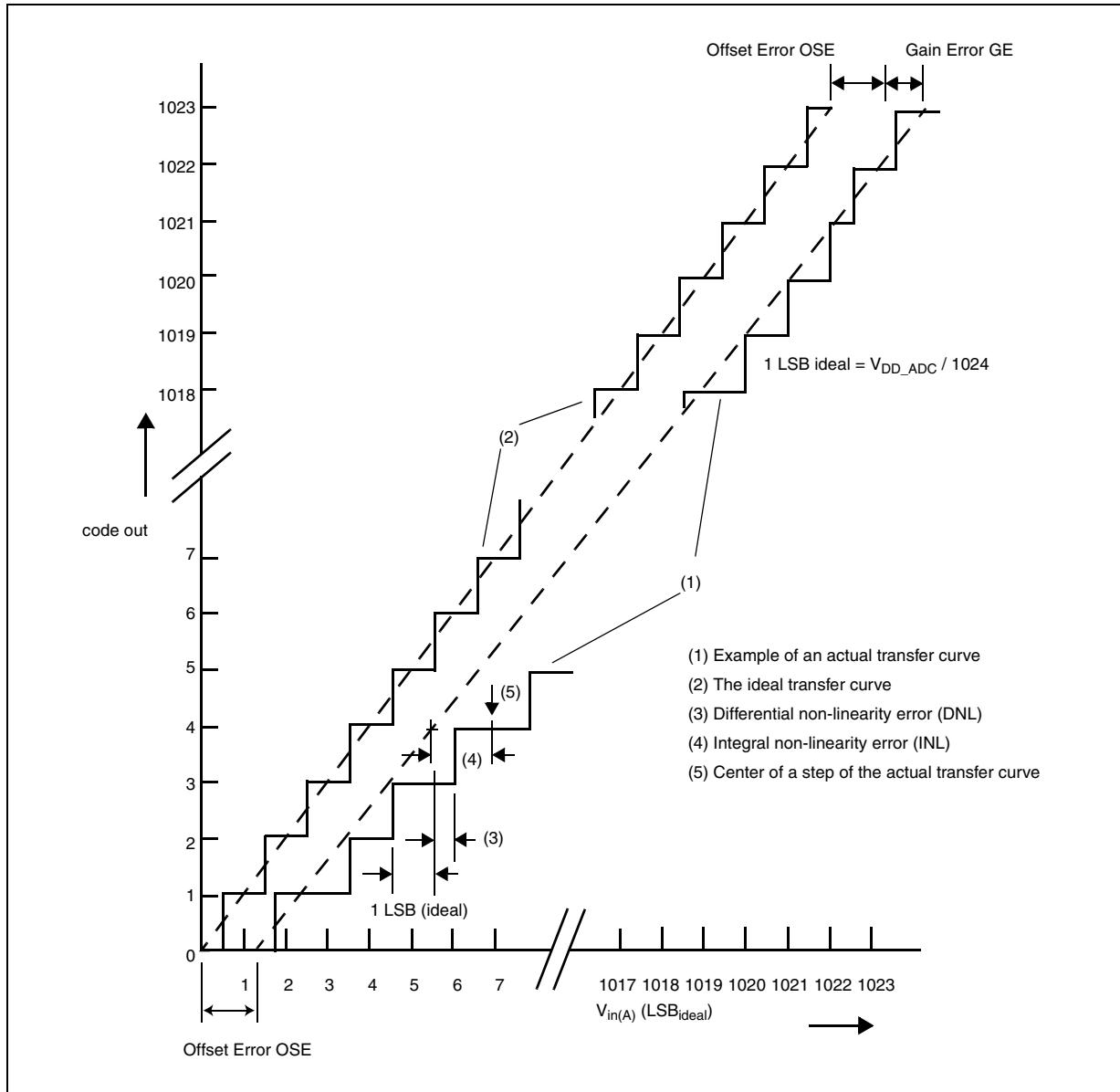


Figure 17. ADC_0 characteristic and error definitions

3.17.2 Input impedance and ADC accuracy

In the following analysis, the input circuit corresponding to the precise channels is considered.

To preserve the accuracy of the A/D converter, it is necessary that analog input pins have low AC impedance. Placing a capacitor with good high frequency characteristics at the input pin of the device can be effective: the capacitor should be as large as

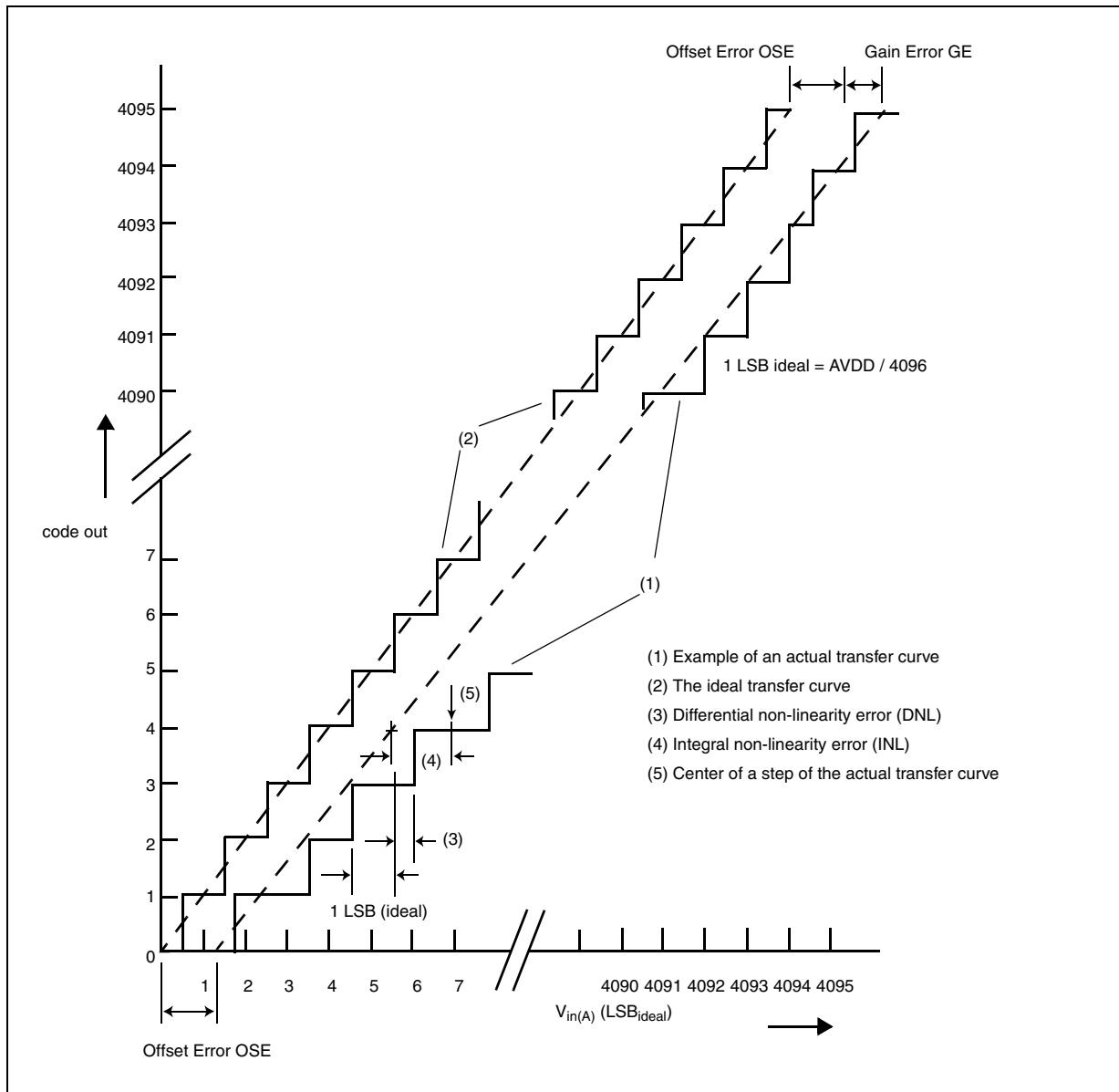


Figure 22. ADC_1 characteristic and error definitions

Table 42. ADC_1 conversion characteristics (12-bit ADC_1)

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
V _{SS_ADC1}	SR	— Voltage on VSS_HV_ADC1 (ADC_1 reference) pin with respect to ground (V _{SS}) ²	—	-0.1	—	0.1	V
V _{DD_ADC1}	SR	— Voltage on VDD_HV_ADC1 pin (ADC_1 reference) with respect to ground (V _{SS})	—	V _{DD} - 0.1	—	V _{DD} + 0.1	V

Table 42. ADC_1 conversion characteristics (12-bit ADC_1) (continued)

Symbol	C	Parameter	Conditions ¹	Value			Unit	
				Min	Typ	Max		
I _{INJ}	SR	— Input current Injection	Current injection on one ADC_1 input, different from the converted one	V _{DD} = 3.3 V ± 10%	—5	—	5	mA
				V _{DD} = 5.0 V ± 10%	—5	—	5	
INLP	CC	T Absolute Integral non-linearity-Precise channels	No overload	—	1	3	LSB	
INLX	CC	T Absolute Integral non-linearity-Extended channels	No overload	—	1.5	5	LSB	
DNL	CC	T Absolute Differential non-linearity	No overload	—	0.5	1	LSB	
OFS	CC	T Absolute Offset error	—	—	2	—	LSB	
GNE	CC	T Absolute Gain error	—	—	2	—	LSB	
TUEP ⁷	CC	P Total Unadjusted Error for precise channels, input only pins	Without current injection	—6	—	6	LSB	
			With current injection	—8	—	8		
TUEX ⁷	CC	T Total Unadjusted Error for extended channel	Without current injection	—10	—	10	LSB	
			With current injection	—12	—	12		

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = —40 to 125 °C, unless otherwise specified

² Analog and digital V_{SS} **must** be common (to be tied together externally).

³ V_{AINx} may exceed V_{SS_ADC1} and V_{DD_ADC1} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0xFFFF.

⁴ During the sample time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_{ADC1_S}. After the end of the sample time t_{ADC1_S}, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_{ADC1_S} depend on programming.

⁵ This parameter does not include the sample time t_{ADC1_S}, but only the time for determining the digital result and the time to load the result's register with the conversion result.

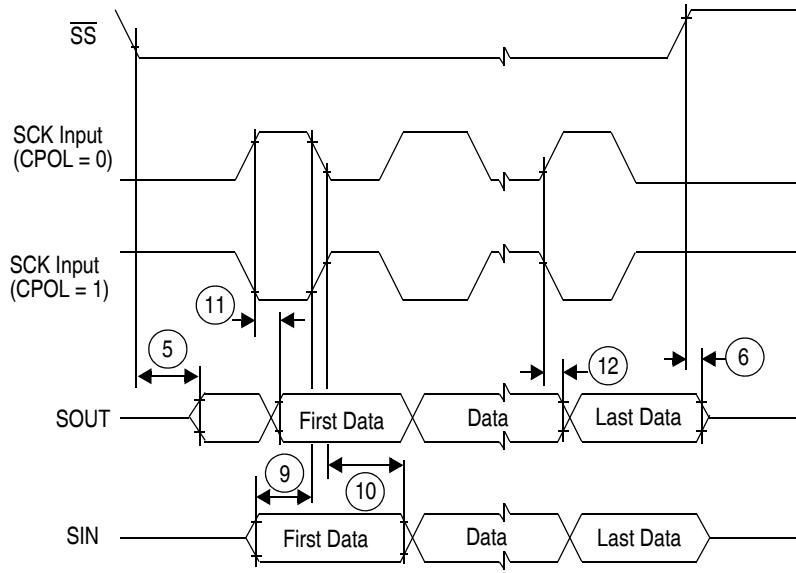
⁶ Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.

⁷ Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.

Table 43. On-chip peripherals current consumption¹ (continued)

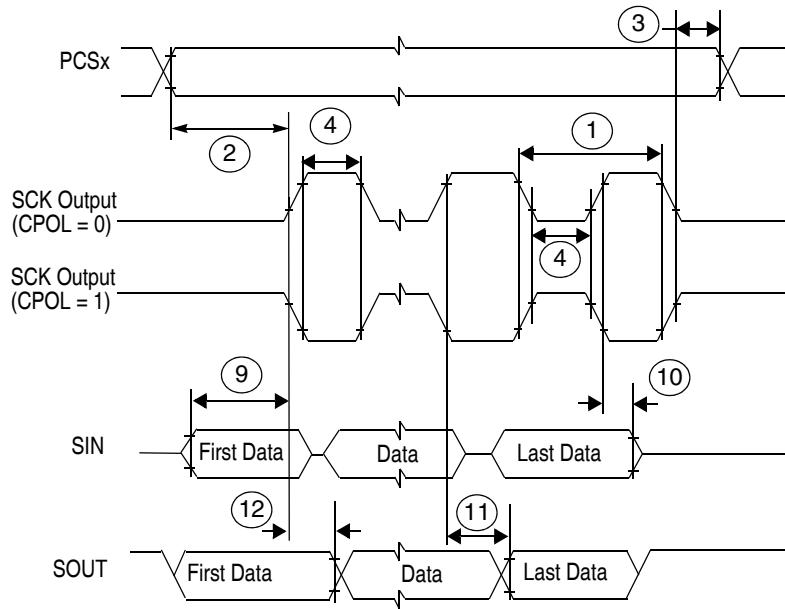
Symbol	C	Parameter	Conditions		Value	Unit	
					Typ		
$I_{DD_HV_ADC1}$	CC	T	ADC_1 supply current on $V_{DD_HV_ADC1}$	$V_{DD} = 5.5\text{ V}$	Analog static consumption (no conversion)	$300 * f_{periph}$	μA
				$V_{DD} = 5.5\text{ V}$	Analog dynamic consumption (continuous conversion)	4	
$I_{DD_HV(FLASH)}$	CC	T	CFlash + DFlash supply current on V_{DD_HV}	$V_{DD} = 5.5\text{ V}$	—	12	mA
$I_{DD_BV(PLL)}$	CC	T	PLL supply current on V_{DD_BV}	$V_{DD} = 5.5\text{ V}$	—	2.5	mA

¹ Operating conditions: $T_A = 25\text{ }^\circ\text{C}$, $f_{periph} = 8\text{ MHz}$ to 64 MHz



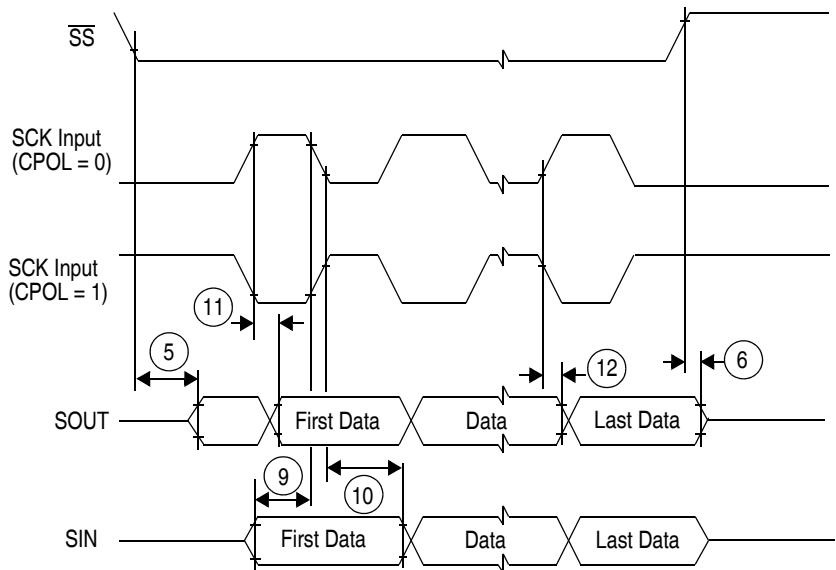
Note: Numbers shown reference [Table 44](#).

Figure 26. DSPI classic SPI timing — slave, CPHA = 1



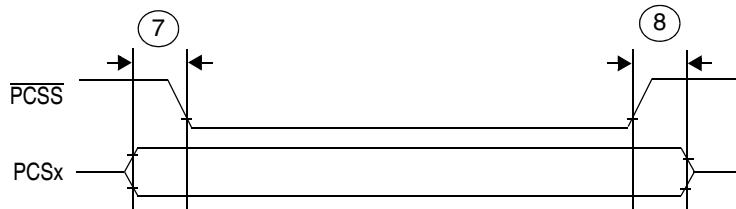
Note: Numbers shown reference [Table 44](#).

Figure 27. DSPI modified transfer format timing — master, CPHA = 0



Note: Numbers shown reference [Table 44](#).

Figure 30. DSPI modified transfer format timing — slave, CPHA = 1



Note: Numbers shown reference [Table 44](#).

Figure 31. DSPI PCS strobe (PCSS) timing

3.18.3 JTAG characteristics

Table 45. JTAG characteristics

No.	Symbol	C	Parameter	Value			Unit	
				Min	Typ	Max		
1	t_{JCYC}	CC	D	TCK cycle time	64	—	—	ns
2	t_{TDIS}	CC	D	TDI setup time	15	—	—	ns
3	t_{TDIH}	CC	D	TDI hold time	5	—	—	ns

Table 45. JTAG characteristics (continued)

No.	Symbol	C	Parameter	Value			Unit
				Min	Typ	Max	
4	t_{TMSS}	CC	D TMS setup time	15	—	—	ns
5	t_{TMSH}	CC	D TMS hold time	5	—	—	ns
6	t_{TDOV}	CC	D TCK low to TDO valid	—	—	33	ns
7	t_{TDOI}	CC	D TCK low to TDO invalid	6	—	—	ns

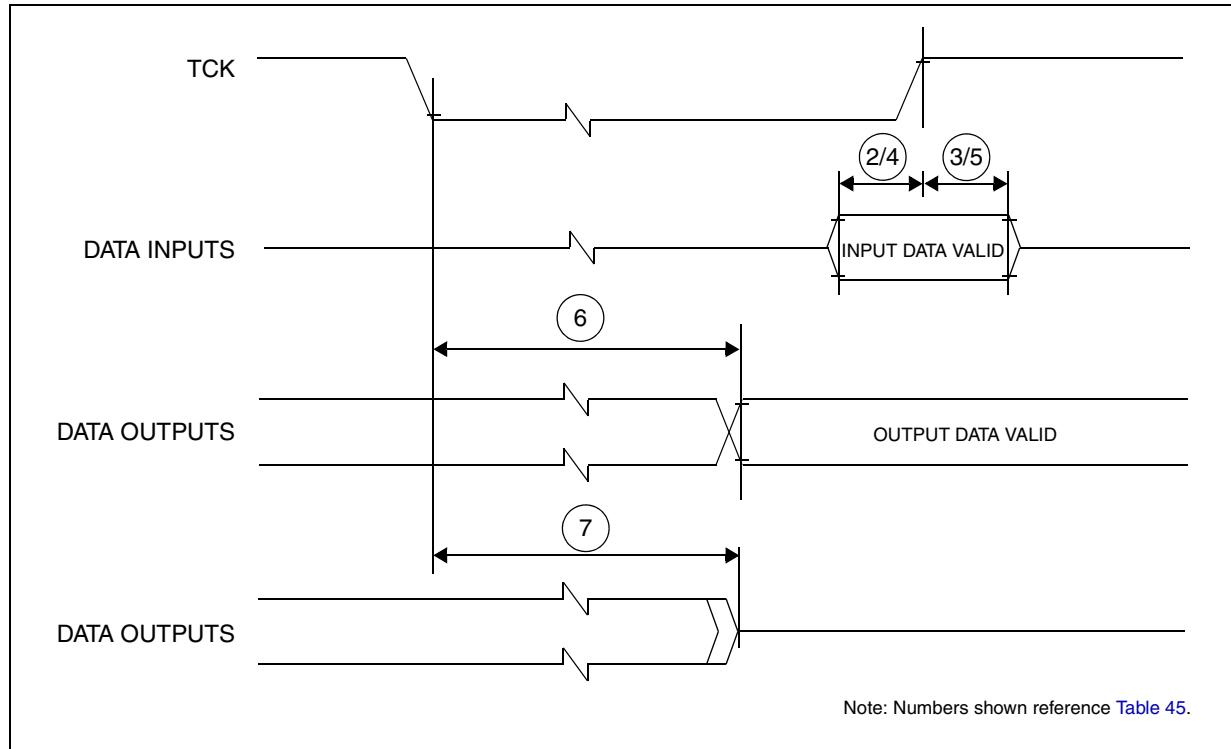


Figure 32. Timing diagram — JTAG boundary scan